













CD4069UB

SCHS054E - NOVEMBER 1998 - REVISED JANUARY 2019

CD4069UB CMOS hex inverter

Features

- Standardized symmetrical output characteristics
- Medium speed operation: t_{PHI} , $t_{PIH} = 30$ ns at 10 V (Typical)
- 100% Tested for quiescent current at 20 V
- Maximum input current of 1 µA at 18 V over full package-temperature range, 100 nA at 18 V and
- Meets all requirements of JEDEC tentative standard No. 13B, Standard Specifications for Description of B Series CMOS Devices

Applications

- Logic inversion
- Pulse shaping
- Oscillators
- High-input-impedance amplifiers

3 Description

The CD4069UB device consist of six CMOS inverter circuits. These devices are intended for all generalpurpose inverter applications where the mediumpower TTL-drive and logic-level-conversion capabilities of circuits such as the CD4009 and CD4049 hex inverter and buffers are not required.

Device Information⁽¹⁾

PART NUMBER	PACKAGE (PINS) BODY SIZE (NOI		
CD4069UBE	PDIP (14)	19.30 mm × 6.35 mm	
CD4069UBF	CDIP (14)	19.56 mm × 6.67 mm	
CD4069UBM	SOIC (14)	8.65 mm × 3.91 mm	
CD4069UBNSR	SO (14)	10.30 mm × 5.30 mm	
CD4069UBPW	TSSOP (14)	5.00 mm × 4.40 mm	

⁽¹⁾ For all available packages, see the orderable addendum at the end of the data sheet.

CD4069UB Functional Diagram

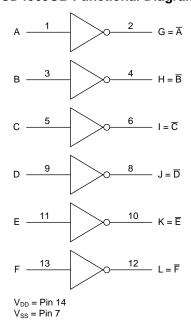




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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

CI	nanges from Revision D (February 2016) to Revision E	Page
•	Removed artifact "-" at t _{PHL} term on the second Features bullet	1
•	Corrected V _I spec MIN/MAX values in the Abs Max Ratings table	4
•	Corrected parameter I _{DD} max term to I _{DD} in the Elec Characteristics table	<mark>5</mark>
•	Corrected parameter I _{OL} min term to I _{OL} in the Elec Characteristics table	5
•	Corrected parameter V _{OL} max term to V _{OL} in the Elec Characteristics table	6
•	Corrected parameter V _{IL} max term to V _{IL} in the Elec Characteristics table	<mark>6</mark>
•	Corrected parameter V _{IH} min term to V _{IH} in the Elec Characteristics table	<mark>6</mark>
•	Corrected parameter I _{IN} max term to I _{IN} in the Elec Characteristics table	<mark>7</mark>
•	Added Y-axis label to Figure 1 image object	8
•	Changed text string from " -t _{PHL} " to "of t _{PHL} " in the Feature Description paragraph.	13

Changes from Revision C (August 2003) to Revision D

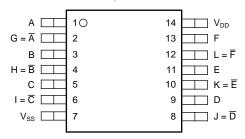
Page

Added ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section



5 Pin Configuration and Functions

D, J, N, NS, and PW Packages 14-Pin PDIP, CDIP, SOIC, SO, and TSSOP Top View



Pin Functions

PIN I/O		1/0	DECODIDATION
NAME	NO.	1/0	DESCRIPTION
Α	1	I	A input
В	3	1	B input
С	5	1	C input
D	9	I	D input
E	11	I	E input
F	13	1	F input
$G = \overline{A}$	2	0	G output
$H = \overline{B}$	4	0	H output
$I = \overline{C}$	6	0	I output
$J = \overline{D}$	8	0	J output
K = E	10	0	K output
L = F	12	0	L output
V _{DD}	14	_	Positive supply
V _{SS}	7	_	Negative supply



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V_{DD}	DC supply-voltage (voltages referenced to $V_{\rm SS}$	terminal)	-0.5	20	V
V_{I}	Input voltage, all inputs		-0.5	$V_{DD} + 0.5$	V
I_{IK}	DC input current, any one input		-10	10	mA
	Power dissipation per package	-55°C to 100°C		500	mW
P_D		100°C to 125°C	12	200	
	Device dissipation per output transistor	Full range (all package types)		100	mW
	Lead temperature (2)			265	°C
T_{J}	Junction temperature			150	°C
T _{stg}	Storage temperature	·	-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

2) During soldering at distance 1/16 inch ± 1/32 inch (1.59 mm ± 0.79 mm) from case for 10 s maximum

6.2 ESD Ratings

			VALUE	UNIT
	Clastrostatia diasharas	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±500	\/
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	±200	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_{DD}	Supply voltage	3	18	V
T _A	Operating temperature	-55	125	°C

6.4 Thermal Information

		CD4069UB						
	THERMAL METRIC ⁽¹⁾	D (SOIC)	J (CDIP)	N (PDIP)	NS (SO)	PW (TSSOP)	UNIT	
		14 PINS	14 PINS	14 PINS	14 PINS	14 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	94.9	_	57.9	91.2	122.1	°C/W	
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	56.4	28.5	45.5	48.8	50.8	°C/W	
$R_{\theta JB}$	Junction-to-board thermal resistance	49.2	_	37.7	50	63.8	°C/W	
ΨЈТ	Junction-to-top characterization parameter	21.1	_	30.6	15	6.3	°C/W	
ΨЈВ	Junction-to-board characterization parameter	48.9	_	37.6	49.6	63.3	°C/W	
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	N/A	°C/W	

 For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.5 Electrical Characteristics - Dynamic

 \underline{T}_{A} = 25°C; input t_{r} , t_{f} = 20 ns; C_{L} = 50 pF; R_{L} = 200 k Ω (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
		$V_{DD}(V) = 5$		55	110	
t_{PLH} , t_{PHL}	Propagation delay time	V _{DD} (V) = 10		30	60	ns
		$V_{DD}(V) = 15$		25	50	
		$V_{DD}(V) = 5$		100	200	
t_{THL}, t_{TLH}	Transition time	$V_{DD}(V) = 10$		50	100	ns
		V _{DD} (V) = 15		40	80	
C _{IN}	Input capacitance	Any input		10	15	pF

6.6 Electrical Characteristics - Static

 $T_A = 25$ °C; input t_r , $t_f = 20$ ns; $C_L = 50$ pF; $R_L = 200$ k Ω (unless otherwise noted)

	PARAMETER	TEST COND	ITIONS	MIN	TYP	MAX	UNIT
			T _A = -55°C			0.25	
			$T_A = -40$ °C			0.25	
		$V_{IN} = 0V \text{ or } 5 \text{ V}$, $V_{DD} = 5 \text{ V}$	T _A = 25°C		0.01	0.25	
		$V_{\text{IN}} = 0 \text{V or } 5 \text{ V , V}_{\text{DD}} = 5 \text{ V} \\ V_{\text{IN}} = 0 \text{V or } 5 \text{ V , V}_{\text{DD}} = 5 \text{ V} \\ V_{\text{IN}} = 0 \text{V or } 5 \text{ V , V}_{\text{DD}} = 5 \text{ V} \\ V_{\text{IN}} = 0 \text{ Or } 10 \text{ V , V}_{\text{DD}} = 5 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V , V}_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}}$	7.5				
			7.5				
PARAMETER I_DD		$T_A = -55$ °C			0.5		
			$T_A = -40$ °C			0.5	
		$V_{IN} = 0 \text{ or } 10 \text{ V}, V_{DD} = 10 \text{ V}$	T _A = 25°C		0.01	0.5	
			T _A = 85°C			15	
$V_{\text{IN}} = 0 \text{ or } 10 \text{ V}, V_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V}, V_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 10 \text{ V}, V_{\text{DD}} = 10 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 15 \text{ V}, V_{\text{DD}} = 15 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 15 \text{ V}, V_{\text{DD}} = 15 \text{ V} \\ V_{\text{IN}} = 0 \text{ or } 20 \text{ V}, V_{\text{DD}} = 20 \text{ V} \\ V_{\text{DD}} = 5 \text{ V} \\ V_{\text{DD}} = 5 \text{ V} \\ V_{\text{DD}} = 20 \text{ C} \\ V_{\text{DD}} = 20$	15	^					
I _{DD}	Quiescent device current		$T_A = -55$ °C			1	μA
						1	
		V _{IN} = 0 or 15 V, V _{DD} = 15 V	T _A = 25°C		0.01	1	
			T _A = 85°C			30	
			T _A = 125°C			30	
		V _{IN} = 0 or 20 V, V _{DD} = 20 V	$T_A = -55$ °C			5	
						5	
			T _A = 25°C		0.02	5	
						150	
						150	
				0.64			
			$T_A = -40$ °C	0.61			
		$V_0 = 0.4 \text{ V}, V_{IN} = 5 \text{ V},$	T _A = 25°C	0.51	1		
		V _{DD} = 3 V	T _A = 85°C	0.42			
			T _A = 125°C	0.36			
Ì				1.6			
				1.5			
I _{OL}	Output low (sink) current	$V_0 = 0.5 \text{ V}, V_{IN} = 10 \text{ V},$		1.3	2.6		mA
-		v _{DD} = 10 v		1.1			
				0.9			
		$V_O = 1.5 \text{ V}, V_{IN} = 15 \text{ V},$		3.4	6.8		
		v _{DD} = 15 v					
I _{OL}							



Electrical Characteristics – Static (continued)

 T_A = 25°C; input t_r , t_f = 20 ns; C_L = 50 pF; R_L = 200 k Ω (unless otherwise noted)

	PARAMETER	TEST CON	IDITIONS	MIN	TYP	MAX	UNIT
			T _A = -55°C	-0.64			
			T _A = -40°C	-0.61			
		$V_O = 4.6 \text{ V}, V_{IN} = 0 \text{ V}, V_{DD} = 5 \text{ V}$	T _A = 25°C	-0.51	-1		
		V DD = 3 V	T _A = 85°C	-0.42			
			T _A = 125°C	$\begin{array}{cccccccccccccccccccccccccccccccccccc$			
			T _A = -55°C	-2			
				-1.8			
		$V_O = 2.5 \text{ V}, V_{IN} = 0 \text{ V}, V_{DD} = 5 \text{ V}$	T _A = 25°C	-1.6	-3.2		
		V DD = 3 V	T _A = 85°C	-1.3			
	Output high (accuracy accuracy		T _A = 125°C	-1.15			Λ
I _{OH}	Output high (source) current		T _A = -55°C	-1.6			mA
			T _A = -40°C	-1.5			
		$V_O = 9.5 \text{ V}, V_{IN} = 0 \text{ V}, V_{DD} = 10 \text{ V}$	T _A = 25°C	-1.3	-2.6		
		VDD = 10 V	T _A = 85°C	-1.1			
			T _A = 125°C	-0.9			
			T _A = -55°C	-4.2			
		$V_{O} = 13.5 \text{ V}, V_{IN} = 0 \text{ V},$ $V_{DD} = 15 \text{ V}$	T _A = -40°C	-4			
			T _A = 25°C	-3.4	-6.8		
			T _A = 85°C	-2.8			
			T _A = 125°C	-2.4			
		V _{IN} = 5 V, V _{DD} = 5 V	T _A = 25°C		0	0.05	
						0.05	
		V _{IN} = 10 V, V _{DD} = 10 V	T _A = 25°C		0	0.05	
V_{OL}	Low-level output voltage		All other			0.05	V
			T _A = 25°C		0	0.05	
		$V_{IN} = 15 \text{ V}, V_{DD} = 15 \text{ V}$	All other			0.05	
V _{OL} Low-leve			-	4.95	5		
		$V_{IN} = 0 V, V_{DD} = 5 V$	All other	4.95			
			-	9.95	10		
V_{OH}	High-level output voltage	$V_{IN} = 0 \ V, \ V_{DD} = 10 \ V$	All other	9.95			V
				14.95	15		
		$V_{IN} = 0 \text{ V}, V_{DD} = 15 \text{ V}$					
			temperatures	14.95			
$V_{O} = 4.5 \text{ V}$		$V_0 = 4.5 \text{ V}, V_{DD} = 5 \text{ V}, \text{ all te}$	emperatures			1	
V_{IL}	Input low voltage	$V_0 = 9 \text{ V}, V_{DD} = 10 \text{ V}, \text{ all te}$	mperatures			2	V
		$V_O = 13.5 \text{ V}, V_{DD} = 15 \text{ V}, \text{ all temperatures}$				2.5	
		$V_0 = 0.5 \text{ V}, V_{DD} = 5 \text{ V}, \text{ all te}$	emperatures	4			
V_{IH}	Input high voltage	$V_O = 1 \text{ V}, V_{DD} = 10 \text{ V}, \text{ all temperatures}$		8			V
		$V_O = 1.5 \text{ V}, V_{DD} = 15 \text{ V}, \text{ all temperatures}$		12.5			

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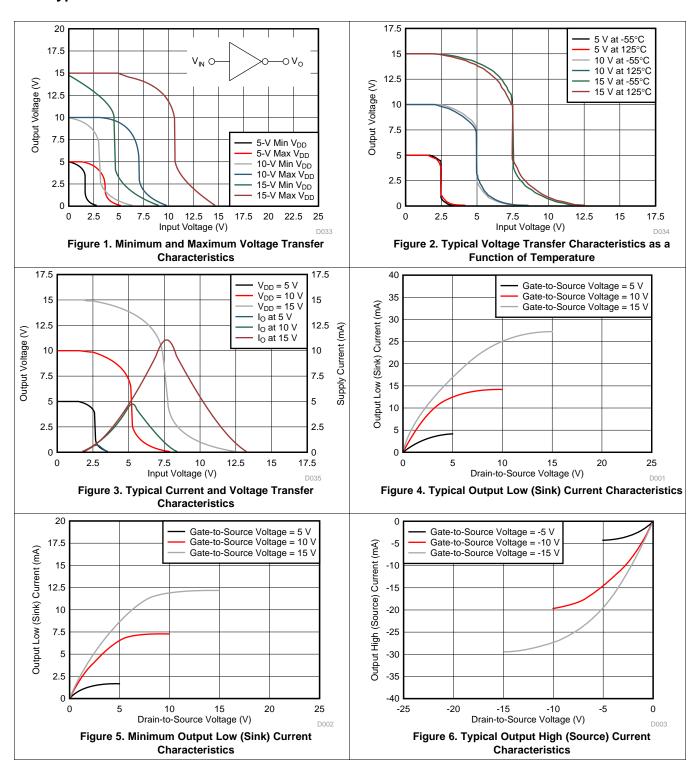
Electrical Characteristics – Static (continued)

 T_A = 25°C; input t_r , t_f = 20 ns; C_L = 50 pF; R_L = 200 k Ω (unless otherwise noted)

	PARAMETER	TEST CONDIT	TIONS	MIN	TYP	MAX	UNIT
		$V_{IN} = 0 V \text{ to } 18 V, V_{DD} = 18 V$	$T_A = -55$ °C			±01	
			$T_A = -40$ °C			±01	
I _{IN}	Input current		T _A = 25°C		±10 ⁻⁵	±1	μΑ
			T _A = 85°C			±1	
			T _A = 125°C			±1	

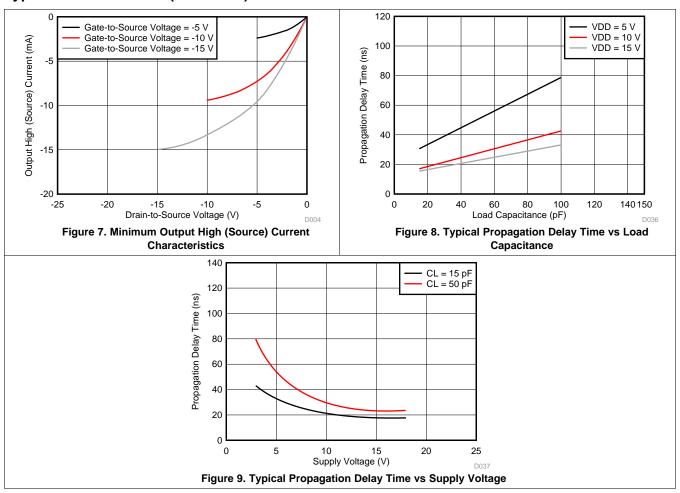
TEXAS INSTRUMENTS

6.7 Typical Characteristics





Typical Characteristics (continued)



7 Parameter Measurement Information

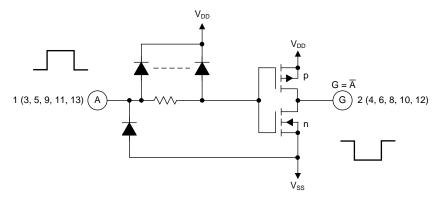


Figure 10. Schematic Diagram of One of Six Identical Inverters

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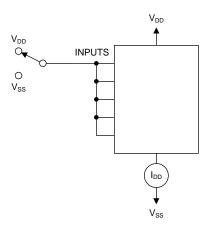


Figure 11. Quiescent Device Current Test Circuit

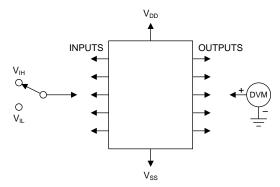


Figure 12. Noise Immunity Test Circuit

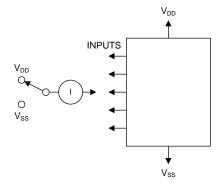


Figure 13. Input Leakage Current Test Circuit



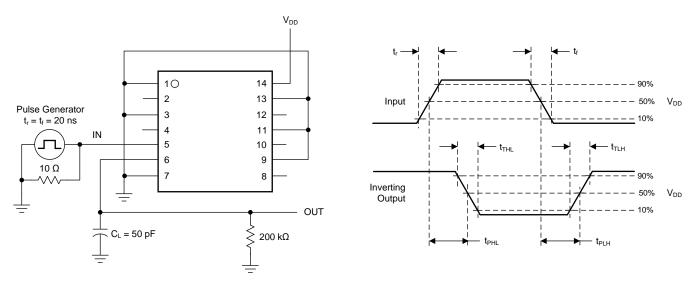


Figure 14. Dynamic Electrical Characteristics Test Circuit and Waveform

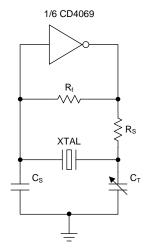


Figure 15. Typical Crystal Oscillator Circuit

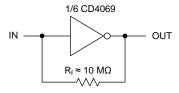


Figure 16. High-Input Impedance Amplifier

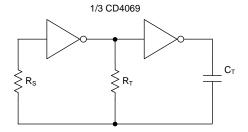


Figure 17. Typical RC Oscillator Circuit



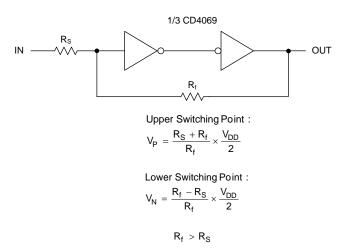


Figure 18. Input Pulse Shaping Circuit

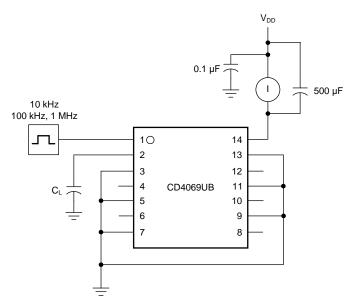


Figure 19. Dynamic Power Dissipation Test Circuit

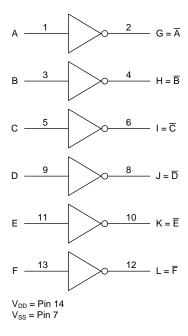


8 Detailed Description

8.1 Overview

The CD4069UB device has six inverter circuits. The recommended operating range is from 3 V to 18 V. The CD4069UB-series types are supplied in 14-pin hermetic dual-in-line ceramic packages (F3A suffix), 14-pin dual-in-line plastic packages (E suffix), 14-pin small-outline packages (M, MT, M96, and NSR suffixes), and 14-pin thin shrink small-outline packages (PW and PWR suffixes).

8.2 Functional Block Diagram



8.3 Feature Description

CD4069UB has standardized symmetrical output characteristics and a wide operating voltage range from 3 V to 18 V with quiescent current tested at 20 V. This has a medium operation speed of t_{PHL}, t_{PLH} = 30 ns (typical) at 10 V. The operating temperature is from –55°C to 125°C. CB4069B meets all requirements of JEDEC tentative standard No. 13B, *Standard Specifications for Description of B Series CMOS Devices*.

8.4 Device Functional Modes

Table 1 shows the functional modes for CD4069UB.

Table 1. Function Table

INPUT A, B, C, D, E, F	OUTPUT G, H, I, J, K, L
Н	L
L	Н



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The CD4069UB device has a low input current of 1 μ A at 18 V over full package-temperature range and 100 nA at 18 V, 25°C. This device has a wide operating voltage range from 3 V to 18 V and used in high voltage applications.

9.2 Typical Application

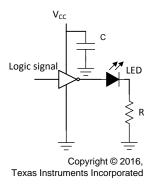


Figure 20. CD4069UB Application

9.2.1 Design Requirements

The CD4069UB device is the industry's highest logic inverter operating at 18 V under recommended conditions. The lower drive capabilities makes it suitable for driving light loads like LED and greatly reduces chances of overshoots and undershoots.

9.2.2 Detailed Design Procedure

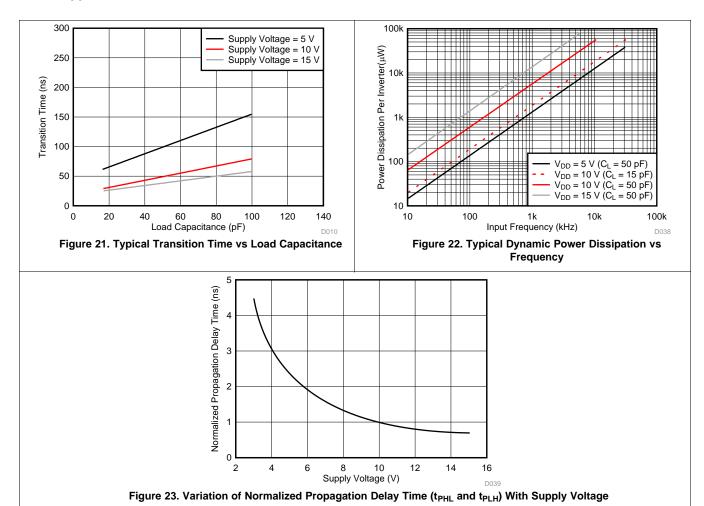
The recommended input conditions for Figure 20 includes rise time and fall time specifications (see $\Delta t/\Delta V$ in Recommended Operating Conditions) and specified high and low levels (see V_{IH} and V_{IL} in Recommended Operating Conditions). Inputs are not overvoltage tolerant and must be below V_{CC} level because of the presence of input clamp diodes to V_{CC} .

The recommended output condition for the CD4069UB application includes specific load currents. Load currents must be limited so as to not exceed the total power (continuous current through V_{CC} or GND) for the device. These limits are located in the *Absolute Maximum Ratings*. Outputs must not be pulled above V_{CC} .



Typical Application (continued)

9.2.3 Application Curves



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10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in *Recommended Operating Conditions*.

Each V_{CC} pin must have a good bypass capacitor to prevent power disturbance. For devices with a single supply, TI recommends a 0.1- μ F capacitor. If there are multiple V_{CC} pins, then TI recommends a 0.01- μ F or 0.022- μ F capacitor for each power pin. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor must be installed as close to the power pin as possible for best results.

11 Layout

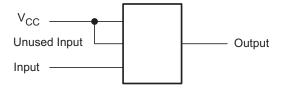
11.1 Layout Guidelines

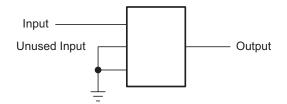
When using multiple bit logic devices, inputs must never float.

In many cases, digital logic device functions or parts of these functions are unused (for example, when only two inputs of a triple-input and gate are used, or only 3 of the 4 buffer gates are used). Such input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. This rule must be observed under all circumstances specified in the next paragraph.

All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. See the application note, *Implications of Slow or Floating CMOS Inputs* (SCBA004), for more information on the effects of floating inputs. The logic level must apply to any particular unused input depending on the function of the device. Generally, they are tied to GND or V_{CC} (whichever is convenient).

11.2 Layout Example







12 Device and Documentation Support

12.1 Device Support

12.1.1 Third-Party Products Disclaimer

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12.2 Documentation Support

12.2.1 Related Documentation

For related documentation see the following:

Implications of Slow or Floating CMOS Inputs, SCBA004

12.3 Community Resource

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

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Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.4 Trademarks

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All other trademarks are the property of their respective owners.

12.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
CD4069UBE	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD4069UBE	Samples
CD4069UBEE4	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD4069UBE	Samples
CD4069UBF	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	CD4069UBF	Samples
CD4069UBF3A	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	CD4069UBF3A	Samples
CD4069UBM	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4069UBM	Samples
CD4069UBM96	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-55 to 125	CD4069UBM	Samples
CD4069UBMT	ACTIVE	SOIC	D	14	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4069UBM	Samples
CD4069UBNSR	ACTIVE	SO	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4069UB	Samples
CD4069UBPW	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CM069UB	Samples
CD4069UBPWG4	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CM069UB	Samples
CD4069UBPWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-55 to 125	CM069UB	Samples
JM38510/17401BCA	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	JM38510/ 17401BCA	Samples
M38510/17401BCA	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	JM38510/ 17401BCA	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

PACKAGE OPTION ADDENDUM

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Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF CD4069UB, CD4069UB-MIL:

Catalog: CD4069UB

Military: CD4069UB-MIL

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD4069UBM96	SOIC	D	14	2500	330.0	16.8	6.5	9.5	2.1	8.0	16.0	Q1
CD4069UBM96	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CD4069UBMT	SOIC	D	14	250	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CD4069UBNSR	so	NS	14	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
CD4069UBPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
CD4069UBPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1



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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CD4069UBM96	SOIC	D	14	2500	364.0	364.0	27.0
CD4069UBM96	SOIC	D	14	2500	356.0	356.0	35.0
CD4069UBMT	SOIC	D	14	250	210.0	185.0	35.0
CD4069UBNSR	SO	NS	14	2000	356.0	356.0	35.0
CD4069UBPWR	TSSOP	PW	14	2000	356.0	356.0	35.0
CD4069UBPWR	TSSOP	PW	14	2000	364.0	364.0	27.0

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
CD4069UBE	N	PDIP	14	25	506	13.97	11230	4.32
CD4069UBE	N	PDIP	14	25	506	13.97	11230	4.32
CD4069UBEE4	N	PDIP	14	25	506	13.97	11230	4.32
CD4069UBEE4	N	PDIP	14	25	506	13.97	11230	4.32
CD4069UBM	D	SOIC	14	50	506.6	8	3940	4.32
CD4069UBPW	PW	TSSOP	14	90	530	10.2	3600	3.5
CD4069UBPWG4	PW	TSSOP	14	90	530	10.2	3600	3.5

MECHANICAL DATA

NS (R-PDSO-G**)

14-PINS SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



CERAMIC DUAL IN LINE PACKAGE



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4040083-5/G





CERAMIC DUAL IN LINE PACKAGE



- 1. All controlling linear dimensions are in inches. Dimensions in brackets are in millimeters. Any dimension in brackets or parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This package is hermitically sealed with a ceramic lid using glass frit.
- His package is remitted by sealed with a ceramic its using glass mit.
 Index point is provided on cap for terminal identification only and on press ceramic glass frit seal only.
 Falls within MIL-STD-1835 and GDIP1-T14.



CERAMIC DUAL IN LINE PACKAGE



D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.



D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



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